



Future Normal in Semiconductor

2025-02-13(목), 10:55-12:40

좌장: 추후업데이트 예정

E. Compound Semiconductors 분과

[TM2-E] WBG Semiconductor-II

<p>TM2-E-1 10:55-11:10</p>	<p>Sub-100 nm Al_{0.4}Ga_{0.6}N/GaN HEMTs with $f_{max} = 490$ GHz Su-Min Choi¹, Hyeok-Jun Lee¹, Wan-Soo Park¹, Hyo-Jin Kim¹, Young-Hun Han², June-O Song², Jae-Hak Lee¹, Kyoungsoon Yang³, and Dae-Hyun Kim¹ ¹Department School of Electronic and Electrical Engineering, Kyungpook National University, ²WaveLord, ³KAIST</p>
<p>TM2-E-2 11:10-11:25</p>	<p>Fabrication and Characterization of GaN FinFETs for Power Devices Hyeon-Tak Kwak¹, Jae-Won Park¹, Dong-Han Kim¹, Hoe-Min Kwak¹, Sung-Bum Bae¹, Hyung-Seok Lee¹, Hyun-Woo Lee^{1,2}, and Sang-Mo Koo² ¹ETRI, ²Department of Electrical Material Engineering, Kwangwoon University</p>
<p>TM2-E-3 11:25-11:40</p>	<p>Enhancement of AlGaIn/GaN HEMTs through N₂ treatment on SiN Passivation Hyo-Jin Kim¹, Su-Min Choi¹, Hyeok-Jun Lee¹, Min-Seo Yoo¹, Yu -Jeong Lee¹, Jae-Hak Lee¹, Kyoungsoon Yang², and Dae-Hyun Kim¹ ¹Kyungpook National University, ²KAIST</p>
<p>TM2-E-4 11:40-11:55</p>	<p>E-mode AlGaIn/GaN HEMTs의 드레인 전압에 의한 문턱전압 열화 분석 채명수, 김형탁 홍익대학교 전자전기공학부</p>
<p>TM2-E-5 11:55-12:10</p>	<p>Device Performance Improvement in GaN-based HEMTs Using Extremely Thin h-BN Passivation Layer and Air Spacer S.-J. Chang¹, S. Moon², D.-S. Kim³, H.-Y. Jung¹, J. Jeong¹, J. Song², J. Kim², H.-K. Ahn¹, Y.-S. Noh¹, J.-W. Lim¹, J. K. Kim², and D.-M. Kang¹ ¹ETRI, ²POSTECH, ³KAERI</p>
<p>TM2-E-6 12:10-12:25</p>	<p>Reducing Thermal Crosstalk in Multi-Finger AlGaIn/GaN HEMTs through Central Source Length Modulation Chae-Yun Lim, Jae-Hun Lee, Tae-Sung Kim, Yeong-Hyun Won, and Hyun-Seok Kim Division of Electronics and Electrical Engineering, Dongguk University</p>



제 32회 한국반도체학술대회

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TM2-E-7 12:25-12:40	<p>Effect of Al-rich AlGa_N Channel Composition Variation on HEMT Performance</p> <p>Joon-Hyuk Lee, Joocheol Jeong, Shyam Mohan, Jooyong Park, Jaejin Heo, and Okhyun Nam</p> <p>CANS, Department of Nano-Semiconductor, Tech University of Korea (TU-Korea)</p>
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